

Surface Mount - 400V - 800V > MAC9DG, MAC9MG, MAC9NG

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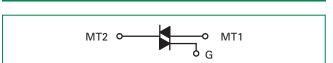
Description

Designed primarily for full-wave ac control applications, such as motor controls, heating controls and power supplies; or wherever half-wave silicon gate-controlled, solid-state devices are needed.

Features

- Blocking Voltage to 800 Volts
- On-State Current Rating of 8.0 Amperes RMS at 100°C
- Uniform Gate Trigger Currents in Three Quadrants
- High Immunity to dv/dt 500 V/µs minimum at 125°C
- Minimizes Snubber Networks for Protection
- Industry Standard TO-220 Package
- High Commutating di/dt 6.5 A/ms minimum at 125°C
- These Devices are Pb-Free and are RoHS Compliant

Functional Diagram



Additional Information



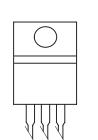




Po

TO-220AB CASE 221A STYLE 4

Pin Out





Maximum Ratings ($T_{J} = 25^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (Gate Open, Sine Wave 50 to 60 Hz, T _J = 25° to 100°C) MAC9N MAC9N	1 RRM	400 600 800	V
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, $T_c = 100^{\circ}C$)	I _{T (RMS)}	8.0	А
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T _J = 125°C)	I _{TSM}	80	A
Circuit Fusing Consideration (t = 8.3 ms)	l²t	26	A ² sec
Peak Gate Power (Pulse Width $\leq 1.0 \ \mu$ s, T _t = 80°C)	P _{GM}	16	W
Average Gate Power (t = 8.3 ms, $T_c = 80^{\circ}$ C)	P _{G (AV)}	0.35	W
Operating Junction Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

Thermal Characteristics						
Rating		Symbol	Value	Unit		
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R _{sjc} R _{sja}	2.2 62.5	°C/W		
Maximum Lead Temperature for Solo 10 seconds	TL	260	°C			



Electrical Characteristics • **OFF** ($T_1 = 25^{\circ}$ C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	$T_{J} = 25^{\circ}C$	I _{DRM} ,	-	-	0.01	mA
$(V_{D} = V_{DRM} = V_{RRM}; Gate Open)$	T _J = 125°C	I _{RRM}	-	-	2.0	mA

Electrical Characteristics - **ON** ($T_J = 25^{\circ}$ C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak On–State Voltage (Note 2) ($I_{TM} = \pm 11 \text{ A}$)		V _{TM}	-	1.2	1.6	V
	MT2(+), G(+)		10	16	50	mA
Gate Trigger Current (Continuous dc)	MT2(+), G(-)	I _{GT}	10	18	50	
$(V_{D} = 12 \text{ V}, \text{ R}_{L} = 100 \Omega)$	MT2(-), G(-)		10	22	5.0	
Holding Current ($V_p = 12 V$, Gate Open, Initiating Current = ±150 mA))			-	30	50	mA
	MT2(+), G(+)		-	20	50	
Latching Current ($V_{D} = 24 \text{ V}, \text{ I}_{G} = 50 \text{ mA}$)	MT2(+), G(-)	I.	_	30	80	mA
	MT2(-), G(-)		_	20	50	
	MT2(+), G(+)		0.5	0.69	1.5	
Gate Trigger Voltage ($V_{D} = 12 \text{ V}, \text{ R}_{L} = 100 \Omega$)	MT2(+), G(-)	V _{GT}	0.5	0.77	1.5	V
	MT2(-), G(-)		0.5	0.72	1.5	
	MT2(+), G(+)		0.2	_	_	
Gate Non–Trigger Voltage ($V_D = 12 \text{ V}, \text{ R}_L = 100 \Omega, \text{ T}_J = 125^{\circ}\text{C}$)	MT2(+), G(–)	V _{gd}	0.2	-	-	V
	MT2(-), G(-)		0.2	_	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Indicates Pulse Test: Pulse Width \leq 2.0 ms, Duty Cycle \leq 2%.

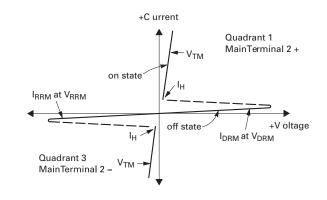
Dynamic Characteristics							
Characteristic	Symbol	Min	Тур	Max	Unit		
Rate of Change of Commutating Current See Figure 10. (V _D = 400 V, I _{TM} = 4.4 A, Commutating dv/dt = 18 V/µs,Gate Open, T _J = 125°C, f = 250 Hz, No Snubber) C _L = 10 µF L _L = 40 mH	dV/dt	6.5	_	_	A/ms		
Critical Rate of Rise of Off-State Voltage ($V_D = Rated V_{DRM}$, Exponential Waveform, $R_{GK} = 510 \Omega$, $T_J = 125$ °C)	dV/dt	500	_	_	V/µs		



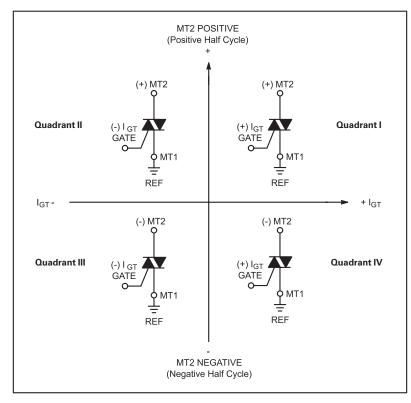
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Voltage Current Characteristic of SCR

Symbol	Parameter
V _{drm}	Peak Repetitive Forward Off State Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Reverse Off State Voltage
I _{RRM}	Peak Reverse Blocking Current
V _{TM}	Maximum On State Voltage
I _H	Holding Current



Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.



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Figure 1. RMS Current Derating

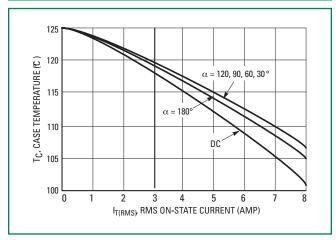


Figure 3. On–State Characteristics

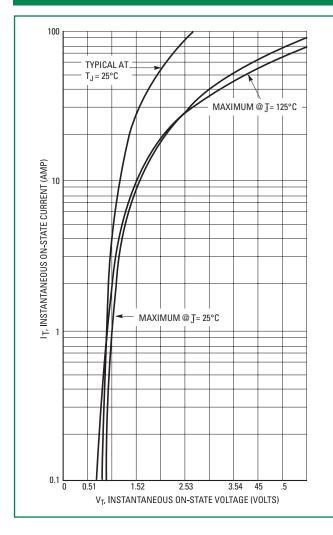


Figure 2. On-State Power Dissipation

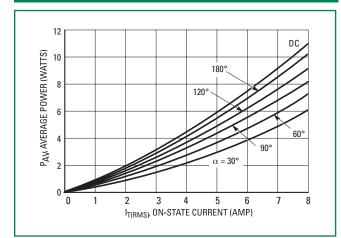


Figure 4. Thermal Response

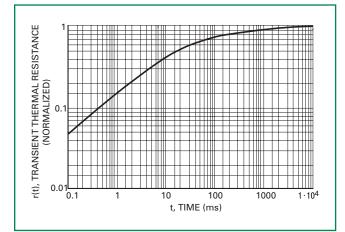
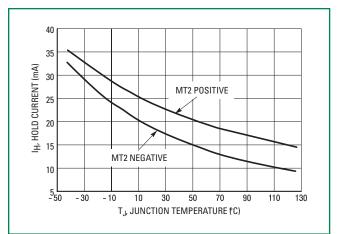


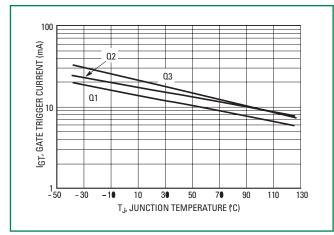
Figure 5. Hold Current Variation





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Figure 6. Gate Trigger Current Variation





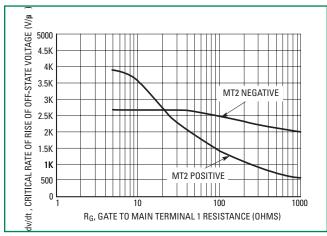


Figure 7. Gate Trigger Voltage Variation

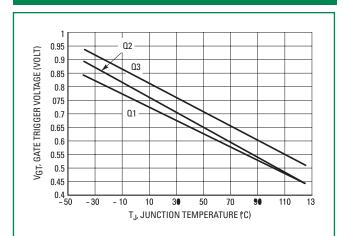


Figure 9. Critical Rate of Rise of CommutatingVoltage

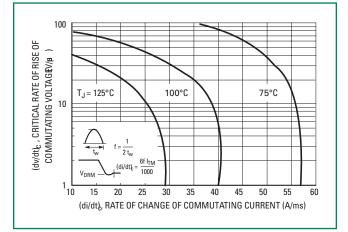
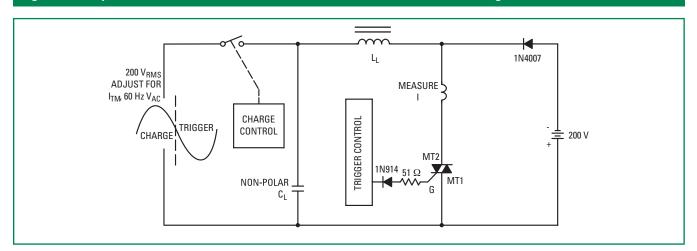


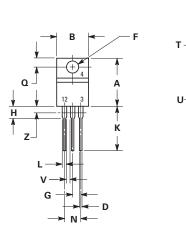
Figure 10. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)

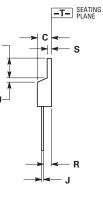




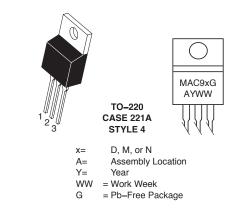
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Dimensions





Part Marking System



Pin Assignment	
1	Main Terminal 1
2	Main Terminal 2
3	Gate
4	Main Terminal 2

Ordering Information

Device	Package	Shipping
MAC9DG		
MAC9MG	TO-220 (Pb-Free)	50 Units / Rail
MAC9NG		

	Inches		Millimeters		
Dim	Min	Max	Min	Max	
А	0.570	0.620	14.48	15.75	
В	0.380	0.405	9.66	10.28	
С	0.160	0.190	4.07	4.82	
D	0.025	0.035	0.64	0.88	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.155	2.80	3.93	
J	0.014	0.022	0.36	0.55	
К	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
N	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.39	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15		
Z		0.080		2.04	

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: INCH.

3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

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